

IN THE SPECIFICATION

Please insert the following heading and paragraph at page 1, between lines 4 and 5:

This application is a divisional of co-pending U.S. Patent Application No. 10/077,757, filed February 20, 2002, the entire contents of which are hereby incorporated herein by reference.

Please amend the heading and the paragraph at page 10, lines 15-26 as follows:

BRIEF SUMMARY OF THE INVENTION

A data writing method for a semiconductor memory device having a first memory cell block capable of rewriting data and having at least one first memory cell, and a second memory cell block capable of rewriting data and having at least one second memory cell adjoining the first memory cell according to ~~a first~~ an aspect of the present invention comprises: writing data into the first memory cell; writing data into the second memory cell ~~adjoining the first memory cell~~ following writing the data into the first memory cell; verifying the data of the first memory cell after writing the data into the second memory cell; and rewriting the data into the first memory cell when insufficiency of the data of the first memory cell as a result of verifying the data of the first memory cell.

Please replace the paragraph at on page 144, lines 2-17 with the following:

A semiconductor memory device includes a first memory cell block capable of rewriting data and having at least one first memory cell, and a second memory cell block capable of rewriting data and having at least one second memory cell adjoining the first memory cell. A data writing method for the semiconductor memory device includes writing data into the first memory cell, writing data into the second memory cell following writing the data into the first memory cell, verifying the data of the first memory cell after writing the data into the second memory cell, and rewriting the data into the first memory cell when insufficiency of the data of the first memory cell as a result of verifying the data of the first memory cell.